

TF2110/TF2113

High-Side and Low-Side Gate Drivers

Features

- Drive two N-channel MOSFETs or IGBTs in high-side / low side configuration
- The floating high-side, drivers drive gates operating at up to 500V / 600V
- 2.5A sink / 2.5A source typical output currents
- Outputs tolerant to negative transients
- Wide gate driver supply voltage range: 10V to 20V
- Wide logic input supply voltage range: 3.3V to 20V
- Wide logic supply offset voltage range: -5V to 5V
- 10 ns (TF2110) / 20 ns (TF2113) maximum delay matching
- 27 ns (typ) rise / 17 ns (typ) fall times with 1000 pF load
- 120 ns (typ) turn-on / 94 ns (typ) turn-off delay times
- Under-voltage lockout for high- and low-side drivers
- Cycle-by-cycle edge-triggered shutdown circuitry
- Extended temperature range: -40 °C to +125 °C
- Drop-in replacements for IR2110 / IR2113

Applications

- DC-DC Converters
- AC-DC Inverters
- Motor Controls
- Class D Power Amplifiers

Description

The TF2110 and TF2113 are high voltage, high-speed MOSFET and IGBT drivers with independent high-side and low-side outputs. The high-side driver features floating supply for operation at up to 500V / 600V. The 10 ns (max) / 20 ns (max) propagation delay matching between the high and the low side drivers allows high frequency operation.

The TF2110 and TF2113 logic inputs are compatible with standard CMOS levels (as low as 3.3V) while driver outputs feature high pulse current buffers designed for minimum driver cross-conduction.

The TF2110 and TF2113 are offered in 16-pin SOIC wide and 14-pin PDIP packages. They operate over an extended -40 $^{\circ}$ C to +125 $^{\circ}$ C temperature range.





PDIP-14

SOIC-16W

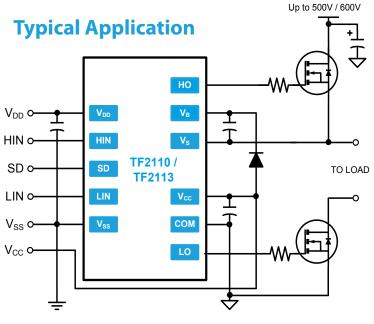
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Ordering Information



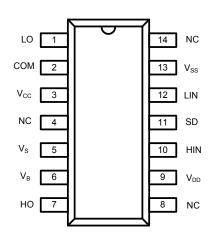
PART NUMBER	PACKAGE	PACK / Qty	MARK
TF2110-3BS	PDIP-14	Tube / 25	YYWW
TF2110-TEU	SOIC-16W	Tube / 47	TF2110
TF2110-TEH	SOIC-16W	T & R / 2500	⊕ Lot ID
TF2113-3BS	PDIP-14	Tube / 25	YYWW
TF2113-TEU	SOIC-16W	Tube / 47	TF2113
TF2113-TEH	SOIC-16W	T & R / 2500	Lot ID

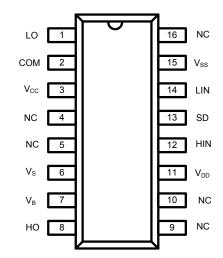




Pin Diagrams

High-Side and Low-Side Gate Drivers





Top View: PDIP-14 **TF2110 / TF2113**

Top View: SOIC-16 Wide **TF2110 / TF2113**

Pin Descriptions

PIN NAME	PIN DESCRIPTION
V _{DD}	Logic power supply pin.
HIN	Logic input pin for the high side gate driver output. HIN and HO are in phase.
SD	Logic input shutdown pin.
LIN	Logic input pin for the low side gate driver output. LIN and LO are in phase.
V _{ss}	Logic ground pin.
V _B	High side gate driver floating power supply pin.
НО	High side gate driver output pin.
V _s	High side gate driver floating power supply return pin.
V _{cc}	Low side gate driver power supply pin.
LO	Low side gate driver output pin.
СОМ	Low side gate driver power supply return pin.
NC	"No connect" pin.



Absolute Maximum Ratings (NOTE1)

V_{B} - High side floating supply voltage (TF2110)0.3V to +525V V_{B} - High side floating supply voltage (TF2113)0.3V to +625V V_{S} - High side floating supply offset voltage V_{B} -25V to V_{B} +0.3V V_{HO} - High side floating output voltage V_{S} -0.3V to V_{B} +0.3V dV_{S} / dt - Offset supply voltage transient50 V/ns
V_{CC} - Low side fixed supply voltage0.3V to +25V V_{LO} - Low side output voltage0.3V to V_{CC} -0.3V
$\rm V_{DD}$ - Logic supply voltage0.3V to $\rm V_{SS}+25V$ $\rm V_{SS}$ - Logic supply offset voltage $\rm V_{CC}$ - 25V to $\rm V_{CC}+0.3V$ $\rm V_{IN}$ - Logic input voltage (HIN, LIN and SD) $\rm V_{SS}$ - 0.3V to $\rm V_{DD}+0.3V$
P_D - Package power dissipation at $T_A \le 25 ^{\circ}\text{C}$ SOIC-16W

NOTE1 Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SOIC-16W Thermal Resistance (NOTE2)	
θ_{IC}	45 °C/W
θ _{JA}	90 °C/W
PDIP-14 Thermal Resistance (NOTE2)	
θ_{JC}	35 °C/W
$ heta_{JA}$	75 °C/W
T ₁ - Junction operating temperature	+150 °C
T ₁ - Lead temperature (soldering, 10s)	+300 °C
T _{sta} - Storage temperature range	55 °C to +150 °C
ESD Susceptibility	
HBM <i>(NOTE3)</i>	2 kV
MM (NOTE4)	200V
CDM <i>(NOTE5)</i>	1.5 kV

NOTE2 When mounted on a standard JEDEC 2-layer FR-4 board. **NOTE3** Human Body Model, applicable standard JESD22-A114

NOTE4 Machine Model, applicable standard JESD22-A115

NOTE5 Field Induced Charge Device Model, applicable standard JESD22-C101

Recommended Operating Conditions

Symbol	Parameter		MIN	TYP	MAX	Unit
V _B	High side floating supply absolute voltage		V _s + 10		V _s + 20	V
V	High side fleating supply offset valte as	TF2110	Note 6		500	V
V_s	High side floating supply offset voltage	TF2113	Note 6		600	V
V _{HO}	High side floating output voltage		V _s		V _B	V
V _{cc}	Low side fixed supply voltage		10		20	V
V _{LO}	Low side output voltage		0		V _{cc}	V
V _{DD}	Logic supply voltage		V _{ss} + 3		V _{ss} + 20	V
V _{ss}	Logic supply offset voltage		-5 (Note 7)		5	V
V _{IN}	Logic input voltage (HIN, LIN and SD)		V _{ss}		V _{DD}	V
T _A	Ambient temperature		-40		125	°C

Note 6 Logic operational for $V_s = -4V$ to +500V. Logic state held for $V_s = -4V$ to $-V_{BS}$.

Note 7 When V_{DD} < 5V, the minimum V_{SS} offset is limited to $-V_{DD}$.



DC Electrical Characteristics (NOTE8)

 $V_{\text{BIAS}}(V_{\text{CC}}, V_{\text{BS}}, V_{\text{DD}}) = 15 \text{V}, T_{\text{A}} = 25 \, ^{\circ}\text{C}$ and $V_{\text{SS}} = \text{COM}$, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
V _{IH}	Logic "1" input voltage		9.5			V
V _{IL}	Logic "0" input voltage				6.0	V
V _{OH}	High level output voltage, V _{BIAS} - V _O	$I_{O} = 0A$			1.2	V
V _{OL}	Low level output voltage, V _o	$I_{O} = 0A$			0.1	V
I _{LK}	Offset supply leakage current	VB = VS = 500V / 600V			50	μΑ
I _{BSQ}	Quiescent V _{BS} supply current	$V_{IN} = 0V \text{ or } V_{DD}$		125	230	μΑ
I _{ccq}	Quiescent V _{cc} supply current	$V_{IN} = 0V \text{ or } V_{DD}$		180	340	μΑ
I _{DDQ}	Quiescent V _{DD} supply current	$V_{IN} = 0V \text{ or } V_{DD}$		15	30	μΑ
I _{IN+}	Logic "1" input bias current	$V_{IN} = V_{DD}$		20	40	μΑ
I _{IN-}	Logic "0" input bias current	V _{IN} = 0V			1	μΑ
V_{BSUV+}	V _{BS} supply under-voltage positive going threshold		7.5	8.6	9.7	V
V _{BSUV} -	V _{BS} supply under-voltage negative going threshold		7.0	8.2	9.4	V
V_{CCUV+}	V _{cc} supply under-voltage positive going threshold		7.4	8.5	9.6	V
V _{CCUV} -	V _{cc} supply under-voltage negative going threshold		7.0	8.2	9.4	V
I _{O+}	Output high short circuit pulsed current	$V_O = 0V, V_{IN} = V_{DD}$ PW \leq 10 \text{ \text{µs}}	2.0	2.5		А
I _{O-}	Output low short circuit pulsed current	$V_{O} = 15V, V_{IN} = 0V$ PW \le 10 \mus	2.0	2.5		А

AC Electrical Characteristics

 $V_{BIAS}(V_{CC}, V_{BS}, V_{DD}) = 15V, T_A = 25$ °C and $V_{SS} = COM$, unless otherwise specified.

Symbol	Parameter		Conditions	MIN	ТҮР	MAX	Unit
t _{on}	Turn-on propagation delay		$V_S = 0V$		120	150	ns
t _{OFF}	Turn-off propagation delay		V _s = 500V / 600V		94	125	ns
t _{SD}	Shut-down propagation delay		V _s = 500V / 600V		110	140	ns
t _r	Turn-on rise time				25	35	ns
t _f	Turn-off fall time				17	25	ns
	Dala material	TF2110				10	ns
t _{DM}	Delay matching	TF2113				20	ns

Note 8 The V_{IW} V_{TH} , and I_{IM} parameters are referenced to V_{SS} and are applicable to all three logic input pins: HIN, LIN and SD. The V_0 and I_0 parameters are referenced to COM and are applicable to the respective output pins: HO and LO.



Timing Diagram and Waveform Definitions

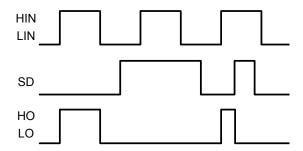


Figure 1. Input / Output Timing Diagram

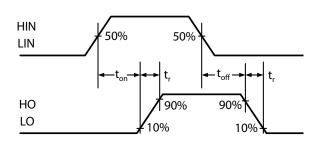


Figure 2. Switching Time Waveform Definition

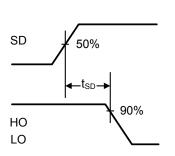


Figure 3. Shutdown Waveform Definitions

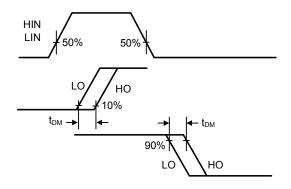
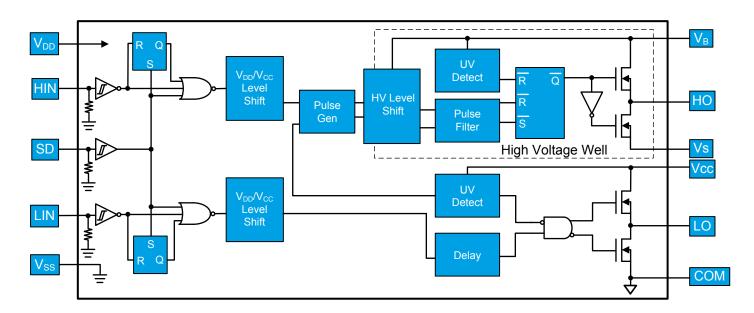


Figure 4. Delay Matching Waveform Definitions

Functional Block Diagram

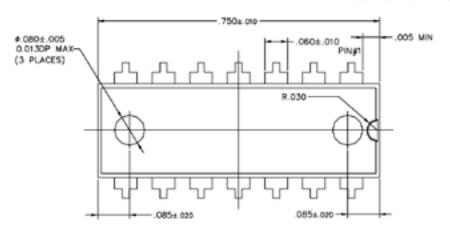


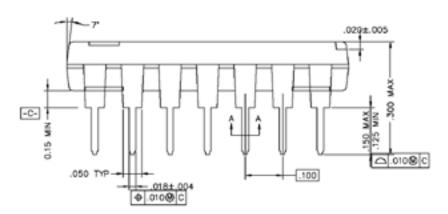


Package Dimensions (PDIP-14)

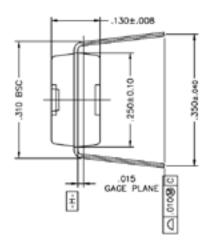
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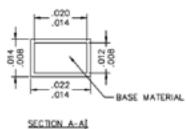
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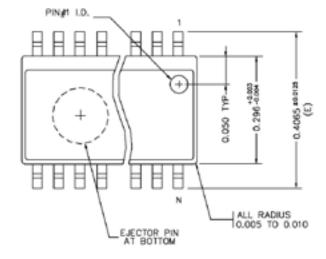




Package Dimensions (SOIC-16 W)

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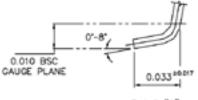


NOTES:

- "D" AND "L" ARE RETERENCE DATAYS AND DO NOT INCLIDE MOLD FLASH OR PROTRUSONS, MOLD FLASH OR PROTRUSONS SHALL NOT EXCEED GLOOP INCHES PER SIDE.
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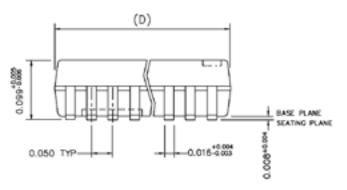
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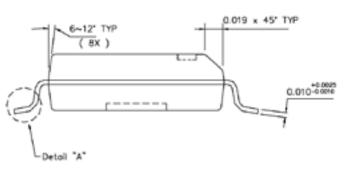
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N	D VARIATIONS				
	MN	NOM	MAX		
16	0.398	0.405	0.412		
20	0.495	0.503	0.510		
24	0.599	0.606	0.613		
28	0.697	0.704	0.711		

Detail "A"







Notes

High-Side and Low-Side Gate Drivers

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